

Surface Mount Low Leakage Diode

BAS116LT1G, S-BAS116LT1G

BAW156LT1G, S-BAW156LT1G

BAV170LT1G, S-BAV170LT1G

BAV199LT1G, S-BAV199LT1G



JXND ELECTRONICS CO.,LTD

FEATURE

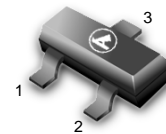
- Ultra-Small Surface Mount Package
- Very Low Leakage Current
- **Lead Free/RoHS Compliant (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL DATA

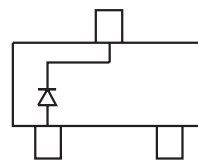
- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Weight: 0.002 grams (approx.)

DEVICE MARKING ORDERING INFORMATION

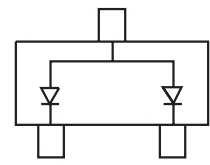
Device	Marking	Shipping
BAS116LT1G S-BAS116LT1G	K50	3000 Tape & Reel
BAS116LT3G S-BAS116LT3G	K50	10000 Tape & Reel
BAW156LT1G S-BAW156LT1G	53	3000 Tape & Reel
BAW156LT3G S-BAW156LT3G	53	10000 Tape & Reel
BAV170LT1G S-BAV170LT1G	51	3000 Tape & Reel
BAV170LT3G S-BAV170LT3G	51	10000 Tape & Reel
BAV199LT1G S-BAV199LT1G	52	3000 Tape & Reel
BAV199LT3G S-BAV199LT3G	52	10000 Tape & Reel



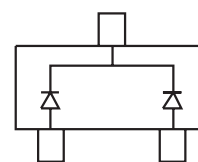
SOT-23



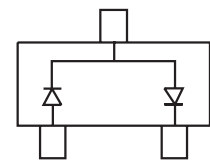
LBAS116LT1G



LBAW156LT1G



LBAV170LT1G



LBAV199LT1G

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	85	V
RMS Reverse Voltage	V _{R(RMS)}	60	V
Forward Continuous Current (Note 1)	I _{FM}	215 125	mA
Repetitive Peak Forward Current	I _{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	4.0 1.0 0.5	A
	@ t = 1.0μs @ t = 1.0ms @ t = 1.0s		
Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance Junction to Ambient Air (Note 1)	R _{θJA}	833	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

Notes: 1. Device mounted on FR-4 PC board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

2. No purposefully added lead.

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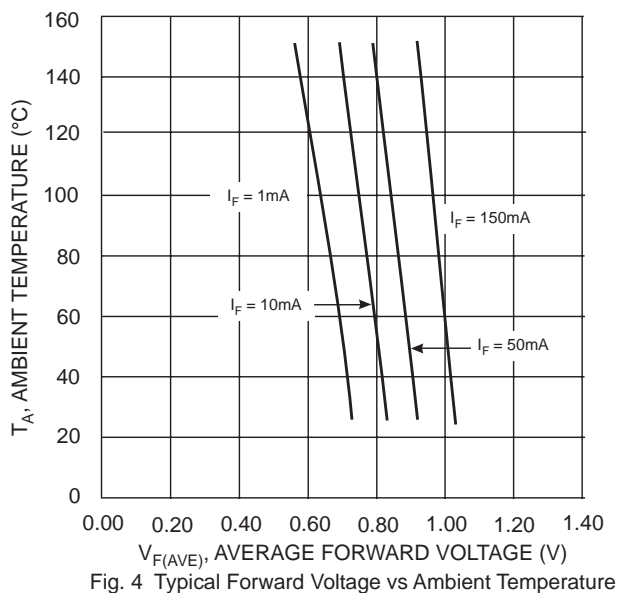
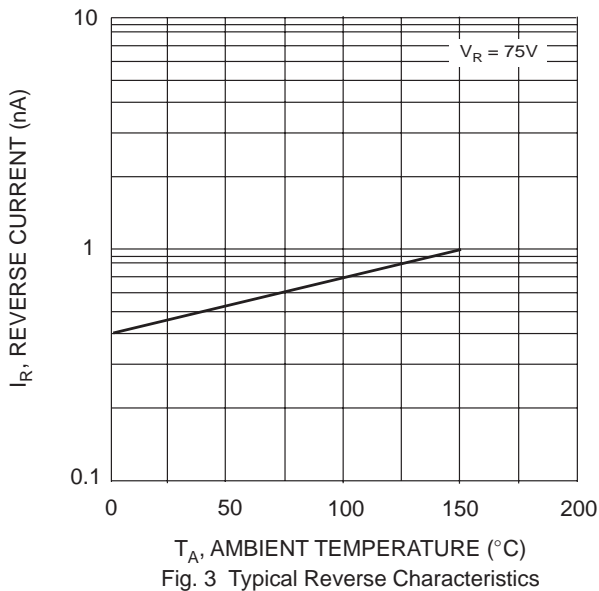
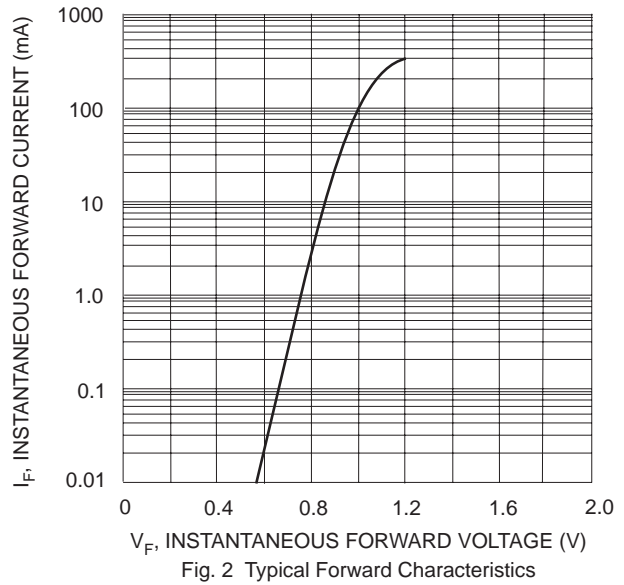
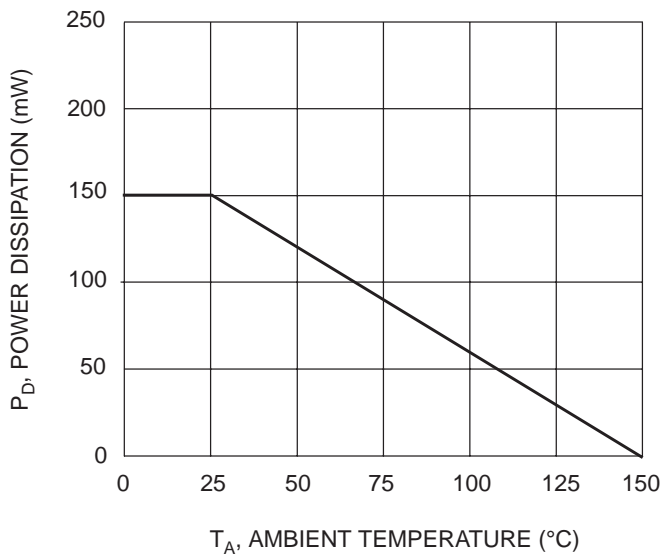
BAV199LT1G, S-BAV199LT1G



Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 3)	$V_{(BR)R}$	85	—	—	V	$I_R = 100\mu\text{A}$
Forward Voltage	V_F	—	—	0.90 1.0 1.1 1.25	V	$I_F = 1.0\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$
Leakage Current (Note 3)	I_R	—	—	5.0 80	nA nA	$V_R = 75\text{V}$ $V_R = 75\text{V}, T_j = 150^\circ\text{C}$
Total Capacitance	C_T	—	2	—	pF	$V_R = 0, f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	—	—	3.0	μs	$I_F = I_R = 10\text{mA}$, $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

Notes: 3. Short duration test pulse used to minimize self-heating effect.



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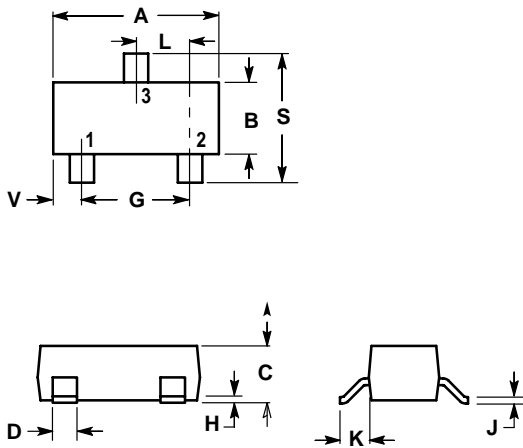
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SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. ANODE
 2. CAHODE
 3. CAHODE/ANODE

